SGS-THOMSON MICROELECTRONICS

STW7NA100
STH7NA100FI

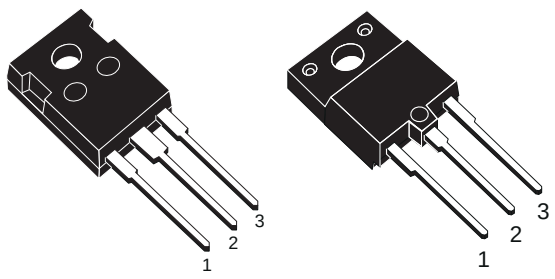
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW7NA100	1000 V	< 1.7 Ω	7 A
STH7NA100FI	1000 V	< 1.7 Ω	4.3 A

- TYPICAL $R_{DS(on)}$ = 1.45 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- GATE CHARGE MINIMISED
- REDUCED THRESHOLD VOLTAGE SPREAD

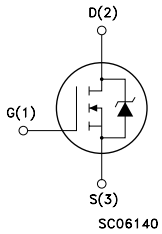
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



TO-247 **ISOWATT218**

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW7NA100	STH7NA100FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	1000		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	1000		V
V_{GS}	Gate-source Voltage	± 30		V
I_D	Drain Current (continuous) at T_c = 25 °C	7	4.3	A
I_D	Drain Current (continuous) at T_c = 100 °C	4.4	2.7	A
I_{DM}(•)	Drain Current (pulsed)	28	28	A
P_{tot}	Total Dissipation at T_c = 25 °C	190	70	W
	Derating Factor	1.52	0.56	W/°C
V_{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

THERMAL DATA

			TO-247	ISOWATT218	
$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.65	1.78	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	30		°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-sink	Typ	0.1		°C/W
T_l	Maximum Lead Temperature For Soldering Purpose		300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	7	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	800	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$	1000			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating $T_c = 100\ ^oC$			50 250	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30$ V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10$V $I_D = 3.5$ A		1.45	1.7	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	7			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 3.5$ A	5	7		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		3170 270 76	4100 351 99	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 500 V I_D = 3.5 A R_G = 4.7 Ω V_{GS} = 10 V		28 19	40 27	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 800 V I_D = 7 A V_{GS} = 10 V		125 17 58	150	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 800 V I_D = 7A R_G = 4.7 Ω V_{GS} = 10 V		35 15 55	50 21 77	ns ns ns

SOURCE DRAIN DIODE

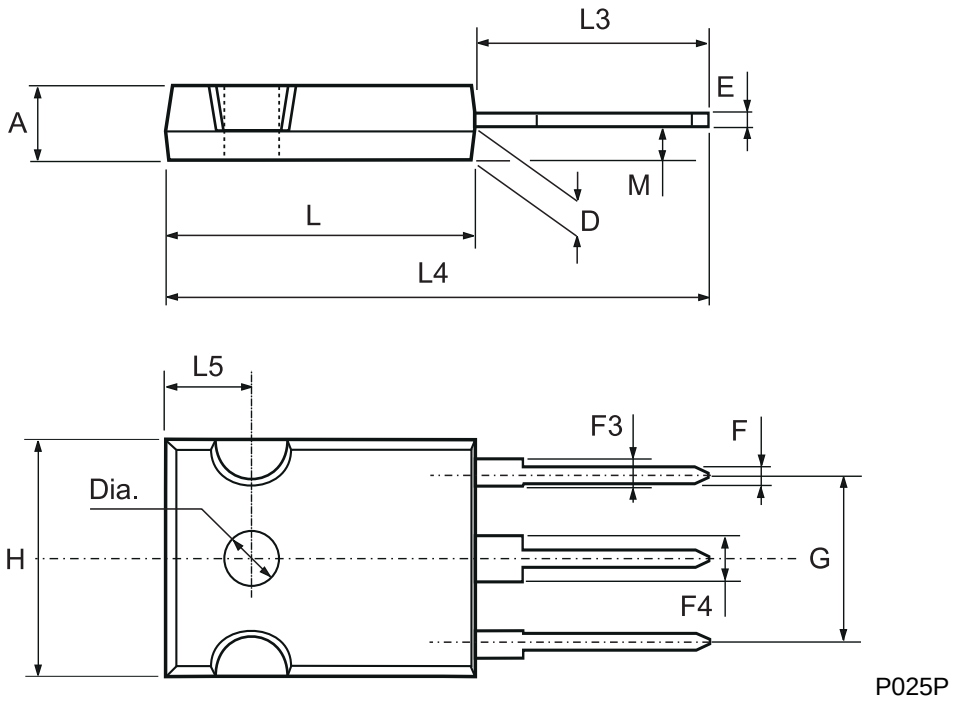
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				7 28	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} = 7 A V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 7 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		835 14 33		ns µC A

(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

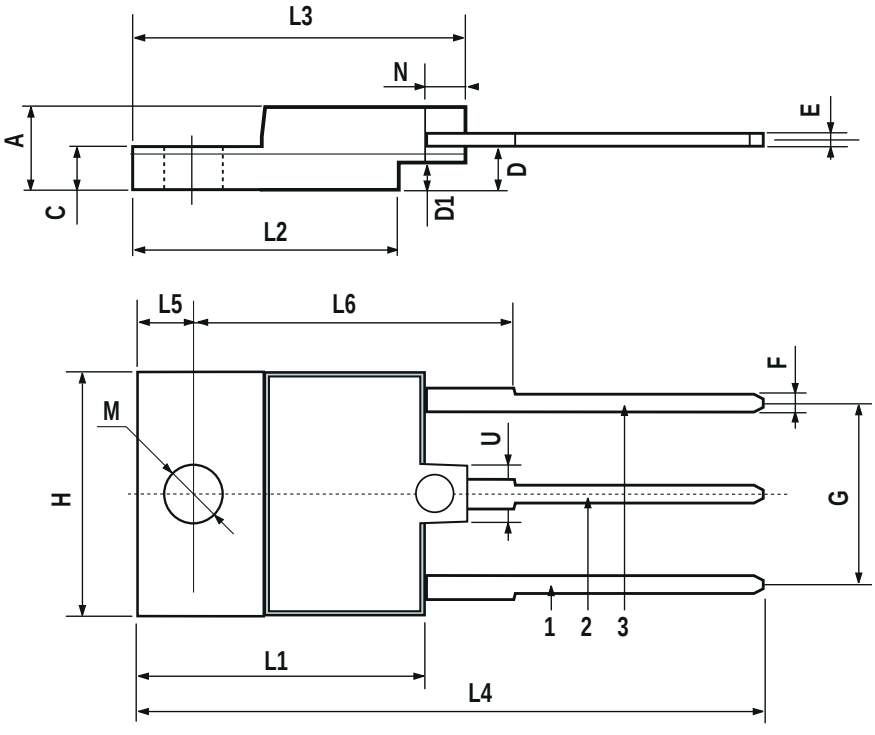
TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144



ISOWATT218 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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